具有三态输出的 CDx4HC573 八路透明 D 类锁存器

1 特性

- 2V 至 6V V_{CC} 运行
- 宽工作温度范围：-55°C 至 125°C
- 三态输出可直接驱动总线
- 平衡的传播延迟及转换时间
- 总线驱动器输出可驱动多达 15 个 LS-TTL 负载
- 与 LS-TTL 逻辑 IC 相比，可显著降低功耗

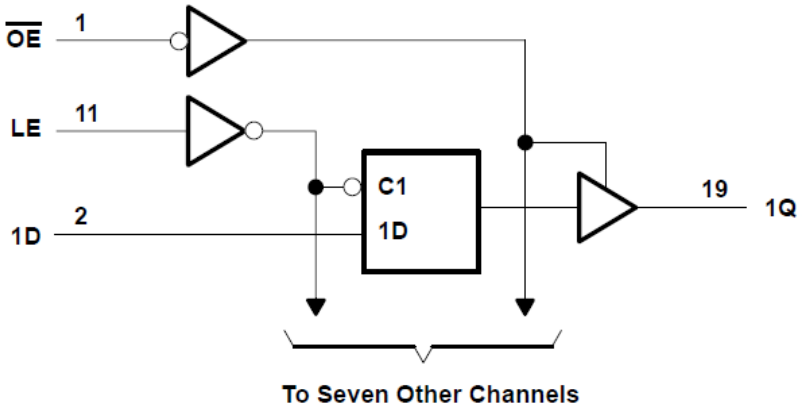
2 说明

HC573 器件为八路透明 D 类锁存器，可在 2V 至 6V V_{CC} 下运行。

器件信息

器件型号	封装[1]	封装尺寸（标称值）
SN74HC574DW	SOIC (20)	12.8mm × 7.50mm
SN74HC574N	PDIP (20)	25.40mm × 6.35mm
SN54HC574J	CDIP (20)	26.92mm × 6.92mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。



功能方框图

内容

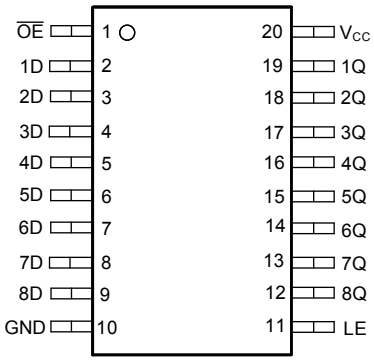
3 Revision History

注：以前版本的页码可能与当前版本的页码不同

Changes from Revision B (January 2022) to Revision C (May 2022)	Page
• Junction-to-ambient thermal resistance values increased. DW was 58 is now 109.1, N was 69 is now 84.6....	4

Changes from Revision A (April 2003) to Revision B (January 2022)	Page
• 更新了整个文档中的编号、格式、表格、图和交叉参考，以反映现代数据表标准.....	1

4 Pin Configuration and Functions



J, N, or DW package
20-Pin CDIP, PDIP, SOIC
Top View

5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage range		–0.5	7	V
I_{IK}	Input clamp current(2)	$V_I < 0$ or $V_I > V_{CC}$		± 20	mA
I_{OK}	Output clamp current(2)	$V_O < 0$ or $V_O > V_{CC}$		± 20	mA
I_O	Continuous output drain current per output	$V_O = 0$ to V_{CC}		± 35	mA
I_O	Continuous output source or sink current per output	$V_O = 0$ to V_{CC}		± 25	mA
	Continuous current through V_{CC} or GND			± 50	mA
T_J	Storage temperature			150	℃
T_{stg}	Storage temperature range		–65	150	℃

(1) Stresses beyond those listed under *absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

5.2 Recommended Operating Conditions(1)

			T_A = 25°C		T_A = –55°C to 125°C		T_A = –40°C to 85°C		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2	6	2	6	2	6	V
V_{IH}	High-level input voltage	V_{CC} = 2 V	1.5		1.5		1.5		V
		V_{CC} = 4.5 V	3.15		3.15		3.15		
		V_{CC} = 6 V	4.2		4.2		4.2		
V_{IL}	Low-level input voltage	V_{CC} = 2 V		0.5		0.5		0.5	V
		V_{CC} = 4.5 V		1.35		1.35		1.35	
		V_{CC} = 6 V		1.8		1.8		1.8	
V_I	Input voltage		0	V_{CC}	0	V_{CC}	0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	0	V_{CC}	0	V_{CC}	V
t_t	Input transition (rise and fall) time	V_{CC} = 2 V		1000		1000		1000	ns
		V_{CC} = 4.5 V		500		500		500	
		V_{CC} = 6 V		400		400		400	

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

5.3 Thermal Information

THERMAL METRIC		DW (SOIC) 20 PINS	N (PDIP) 20 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance(1)	109.1	84.6	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	76	72.5	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	77.6	65.3	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	51.5	55.3	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	77.1	65.2	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC package thermal metrics* application report.

5.4 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}	T_A = 25°C		T_A = –55°C to 125°C		TA_A = –40°C to 85°C		UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	
V_{OH}	V_I = V_{IH} or V_{IL}	I_{OH} = –20 μA	2 V	1.9		1.9		1.9		V
			4.5 V	4.4		4.4		4.4		
			6 V	5.9		5.9		5.9		
		I_{OH} = –6 mA	4.5 V	3.98		3.7		3.84		
		I_{OH} = –7.8 mA	6 V	5.48		5.2		5.34		
V_{OL}	V_I = V_{IH} or V_{IL}	I_{OL} = 20 μA	2 V		0.1		0.1		0.1	V
			4.5 V		0.1		0.1		0.1	
			6 V		0.1		0.1		0.1	
		I_{OL} = 6 mA	4.5 V		0.26		0.4		0.33	
		I_{OL} = 7.8 mA	6 V		0.26		0.4		0.33	
I_I	V_I = V_{CC} or 0		6 V		±0.1		±1		±1	μA
I_{OZ}	V_O = V_{CC} or 0		6 V		±0.5		±10		±5	μA
I_{CC}	V_I = V_{CC} or 0,	I_O = 0	6 V		8		160		80	μA
C_i					10		10		10	pF
C_o					20		20		20	pF

5.5 Timing Requirements

over recommended operating free-air temperature range (unless otherwise noted) (see 图 6-1)

		V_{CC}	T_A = 25°C		T_a = –55°C to 125°C		T_a = –40°C to 85°C		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t_w	Pulse duration, LE high	2 V	80		120		100		ns
		4.5 V	16		24		20		
		6 V	14		20		17		
t_{su}	Setup time, data before LE ↓	2 V	50		75		65		ns
		4.5 V	10		15		13		
		6 V	9		13		11		
t_h	Hold time, data after LE ↓	2 V	40		60		50		ns
		4.5 V	8		12		10		
		6 V	7		10		9		

5.6 Switching Characteristics

over recommended operating free-air temperature range (unless otherwise noted) (see 图 6-1)

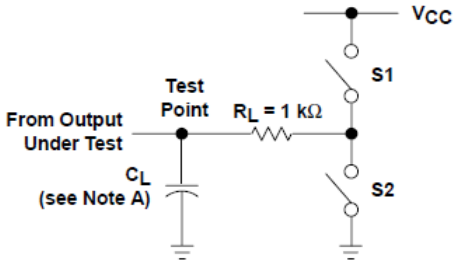
PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	V_{CC}	T_A = 25°C		T_A = –55°C to 125°C		T_A = –40°C to 85°C		UNIT
					MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	D	Q	C_L = 50 pF	2 V		175		265		220	ns
				4.5 V		35		53		44	
				6 V		30		45		37	
	LE	Q	C_L = 50 pF	2 V		175		265		220	
				4.5 V		35		53		44	
				6 V		30		45		37	
t_{en}	$\overline{OE}$	Q	C_L = 50 pF	2 V		150		225		190	ns
				4.5 V		30		45		38	
				6 V		26		38		33	
t_{dis}	$\overline{OE}$	Q	C_L = 50 pF	2 V		150		225		190	ns
				4.5 V		30		45		38	
				6 V		26		38		33	
t_t		Q	C_L = 50 pF	2 V		60		90		75	ns
				4.5 V		12		18		15	
				6 V		10		15		13	

5.7 Operating Characteristics

V_{CC} = 5 V, T_A = 25℃

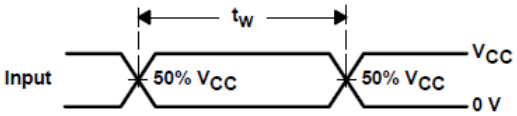
PARAMETER		TYP	UNIT
C_{pd}	Power dissipation capacitance	51	pF

6 Parameter Measurement Information

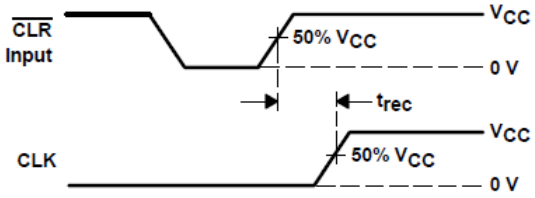


LOAD CIRCUIT

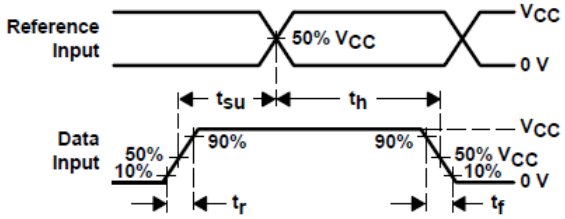
PARAMETER		S1	S2
t_{en}	t_{PZH}	Open	Closed
	t_{PZL}	Closed	Open
t_{dis}	t_{PHZ}	Open	Closed
	t_{PLZ}	Closed	Open
t_{pd} or t_t		Open	Open



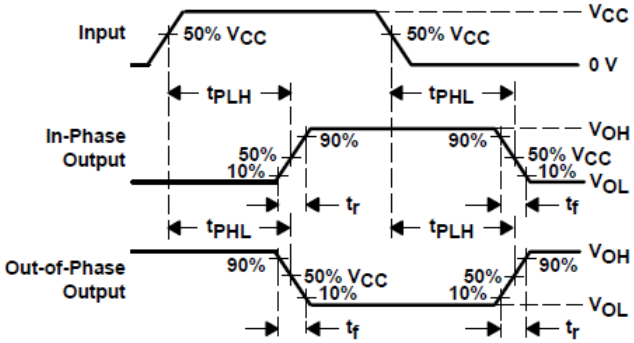
VOLTAGE WAVEFORMS
PULSE DURATION



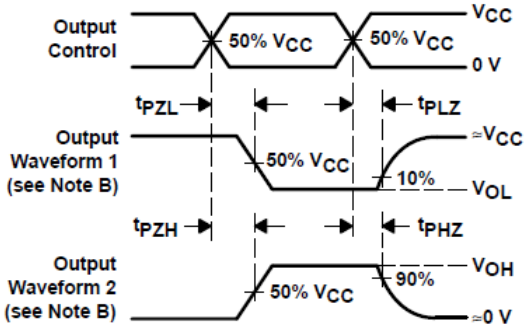
VOLTAGE WAVEFORMS
RECOVERY TIME



VOLTAGE WAVEFORMS
SETUP AND HOLD AND INPUT RISE AND FALL TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY AND OUTPUT TRANSITION TIMES



VOLTAGE WAVEFORMS
OUTPUT ENABLE AND DISABLE TIMES

A. C_L includes probe and test-fixture capacitance
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control.Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control
C. Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: PRR ⩽ 1 MHz, Z_O = 50 Ω, t_r = 6 ns, t_f = 6 ns
D. For clock inputs, f_{max} is measured with the input duty cycle at 50%
E. The outputs are measured one at a time with one input transition per measurement
F. t_{PLZ} and t_{PHZ} are the same as t_{dis}
G. t_{PZL} and t_{PZH} are the same as t_{en}
H. t_{PLH} and t_{PHL} are the same as t_{pd}

图 6-1. Load Circuit and Voltage Waveforms

7 Detailed Description

7.1 Overview

The ’HC573 devices are octal transparent D-type latches designed for 2-V to 6-V V_{CC} operation.

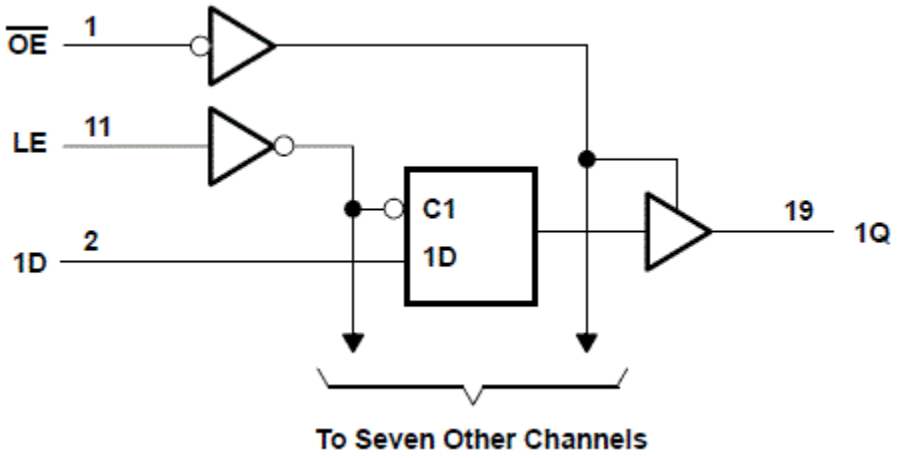
When the latch-enable (LE) input is high, the Q outputs follow the data (D) inputs. When LE is low, the Q outputs are latched at the logic levels of the D inputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low) or the high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without interface or pullup components.

$\overline{OE}$ does not affect the internal operations of the latches. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

7.2 Functional Block Diagram



7.3 Device Functional Modes

表 7-1. Function Table (each latch)

INPUTS			OUTPUTQ
$\overline{OE}$	LE	D	
L	H	H	H
L	H	L	L
L	L	X	Q_0
H	X	X	Z

8 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. A 0.1-μF capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1-μF and 1-μF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

9 Layout

9.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC}, whichever makes more sense for the logic function or is more convenient.

10 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

10.1 接收文档更新通知

要接收文档更新通知，请导航至 ti.com 上的器件产品文件夹。点击 *订阅更新* 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

10.2 支持资源

TI E2E™ 支持论坛是工程师的重要参考资料，可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题可获得所需的快速设计帮助。

链接的内容由各个贡献者“按原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的《使用条款》。

10.3 Trademarks

TI E2E™ is a trademark of Texas Instruments.
所有商标均为其各自所有者的财产。

10.4 Electrostatic Discharge Caution

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

10.5 术语表

TI 术语表	本术语表列出并解释了术语、首字母缩略词和定义。

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CD54HC573F	ACTIVE	CDIP	J	20	20	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	CD54HC573F	Samples
CD54HC573F3A	ACTIVE	CDIP	J	20	20	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	8512801RA CD54HC573F3A	Samples
CD74HC573E	ACTIVE	PDIP	N	20	20	RoHS & Green	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HC573E	Samples
CD74HC573EE4	ACTIVE	PDIP	N	20	20	RoHS & Green	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HC573E	Samples
CD74HC573M96	ACTIVE	SOIC	DW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HC573M	Samples
CD74HC573M96G4	ACTIVE	SOIC	DW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HC573M	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

OTHER QUALIFIED VERSIONS OF CD54HC573, CD74HC573 :

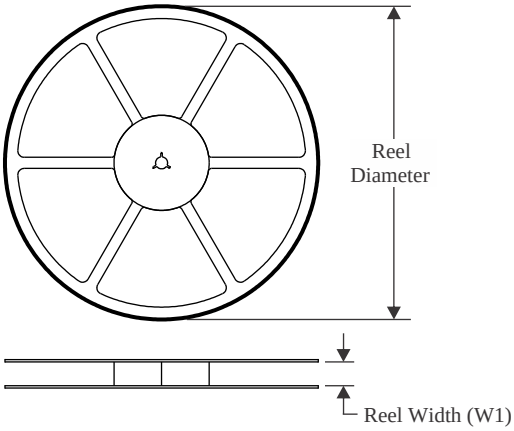
- Catalog : CD74HC573
- Military : CD54HC573

NOTE: Qualified Version Definitions:

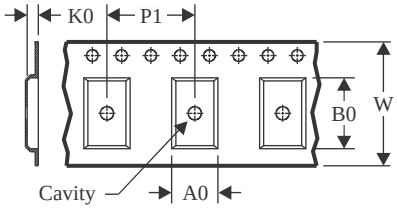
- Catalog - TI's standard catalog product
- Military - QML certified for Military and Defense Applications

TAPE AND REEL INFORMATION

REEL DIMENSIONS

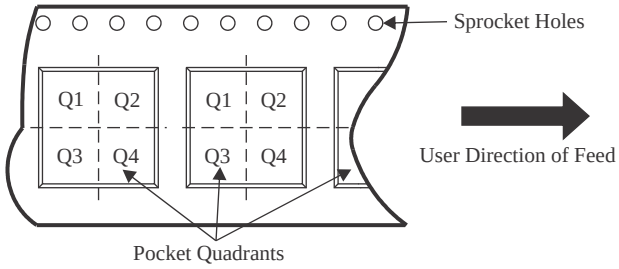


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

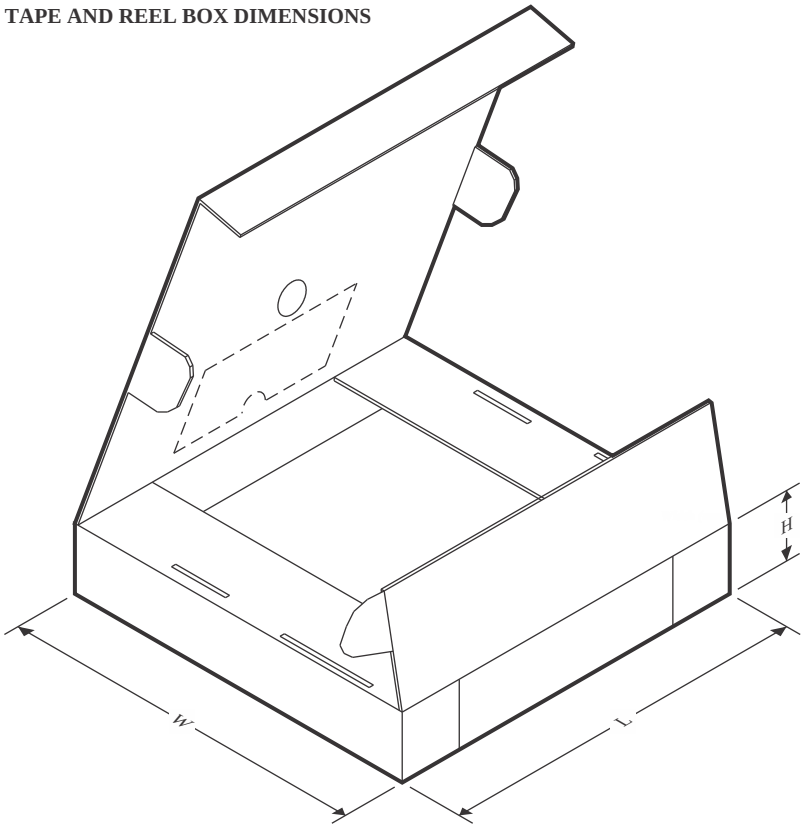
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CD74HC573M96	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
CD74HC573M96	SOIC	DW	20	2000	330.0	24.4	10.9	13.3	2.7	12.0	24.0	Q1

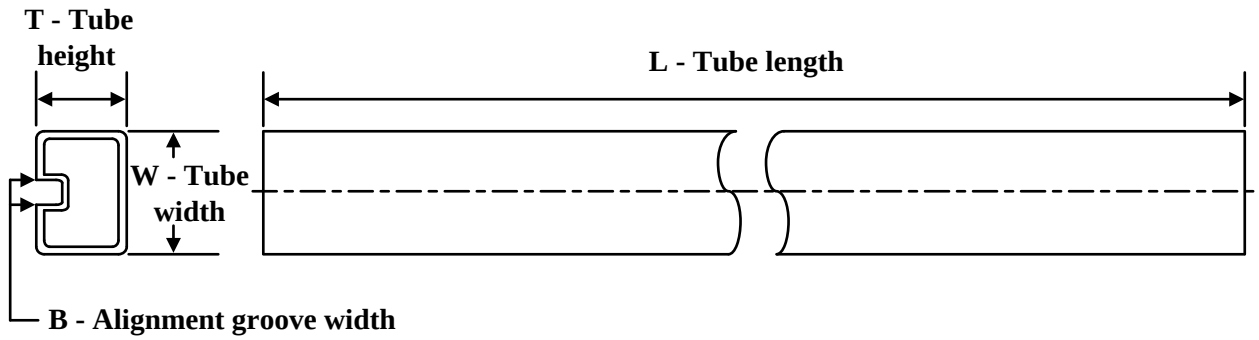
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CD74HC573M96	SOIC	DW	20	2000	367.0	367.0	45.0
CD74HC573M96	SOIC	DW	20	2000	367.0	367.0	45.0

TUBE



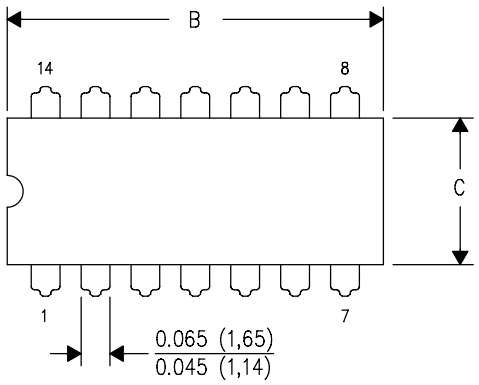
*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
CD74HC573E	N	PDIP	20	20	506	13.97	11230	4.32
CD74HC573EE4	N	PDIP	20	20	506	13.97	11230	4.32

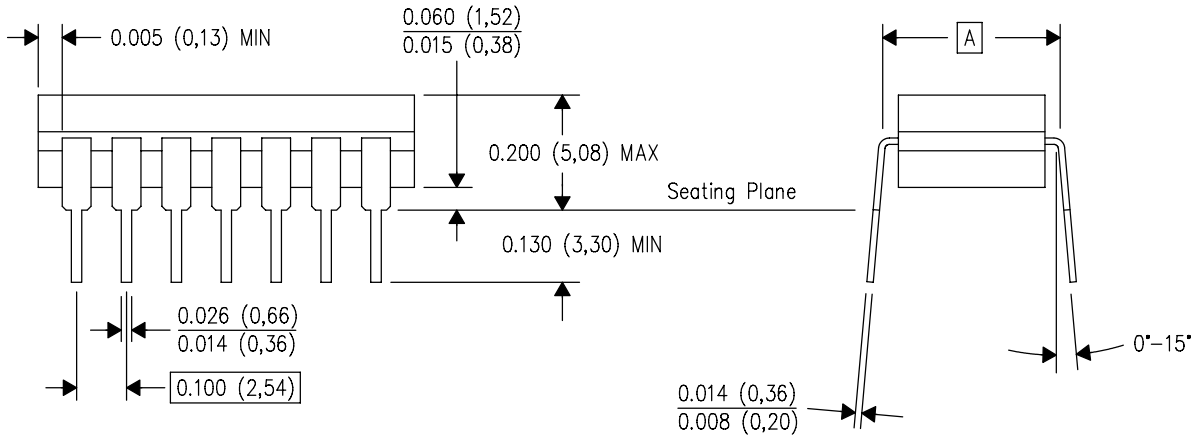
J (R–GDIP–T**)

14 LEADS SHOWN

CERAMIC DUAL IN–LINE PACKAGE



DIM \ PINS **	14	16	18	20
A	0.300 (7,62) BSC	0.300 (7,62) BSC	0.300 (7,62) BSC	0.300 (7,62) BSC
B MAX	0.785 (19,94)	.840 (21,34)	0.960 (24,38)	1.060 (26,92)
B MIN	—	—	—	—
C MAX	0.300 (7,62)	0.300 (7,62)	0.310 (7,87)	0.300 (7,62)
C MIN	0.245 (6,22)	0.245 (6,22)	0.220 (5,59)	0.245 (6,22)



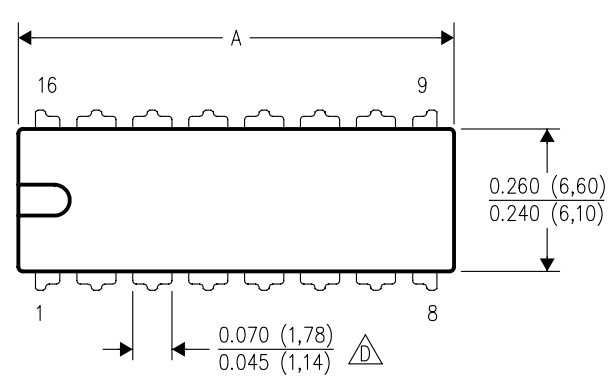
4040083/F 03/03

NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. This package is hermetically sealed with a ceramic lid using glass frit.
D. Index point is provided on cap for terminal identification only on press ceramic glass frit seal only.
E. Falls within MIL STD 1835 GDIP1–T14, GDIP1–T16, GDIP1–T18 and GDIP1–T20.

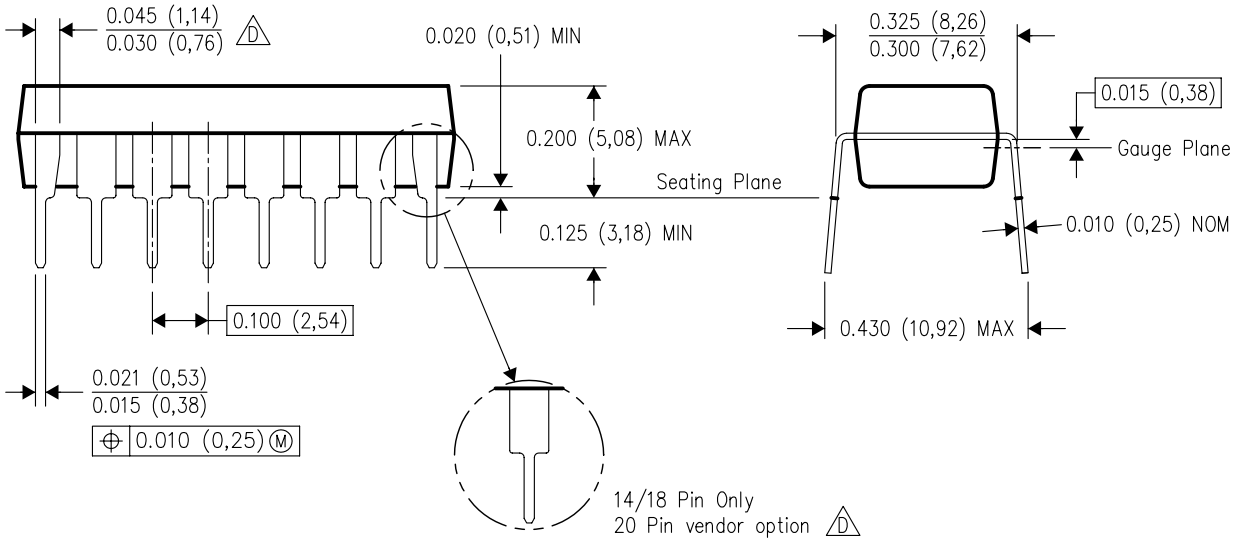
N (R–PDIP–T**)

PLASTIC DUAL–IN–LINE PACKAGE

16 PINS SHOWN

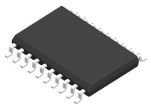


DIM \ PINS **	14	16	18	20
A MAX	0.775 (19,69)	0.775 (19,69)	0.920 (23,37)	1.060 (26,92)
A MIN	0.745 (18,92)	0.745 (18,92)	0.850 (21,59)	0.940 (23,88)
MS–001 VARIATION (C)	AA	BB	AC	AD



4040049/E 12/2002

NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Falls within JEDEC MS–001, except 18 and 20 pin minimum body length (Dim A).
D. The 20 pin end lead shoulder width is a vendor option, either half or full width.

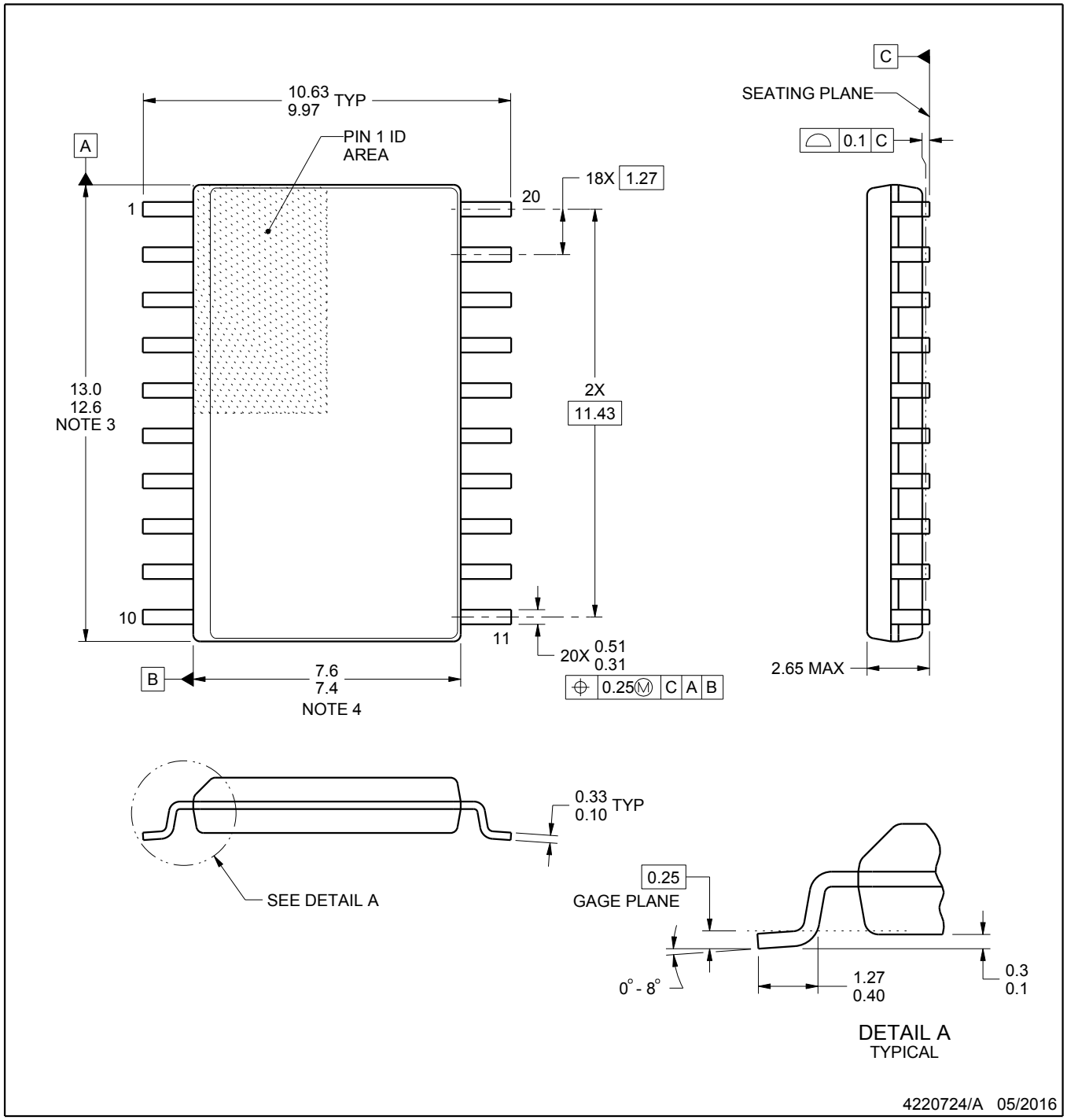


PACKAGE OUTLINE

DW0020A

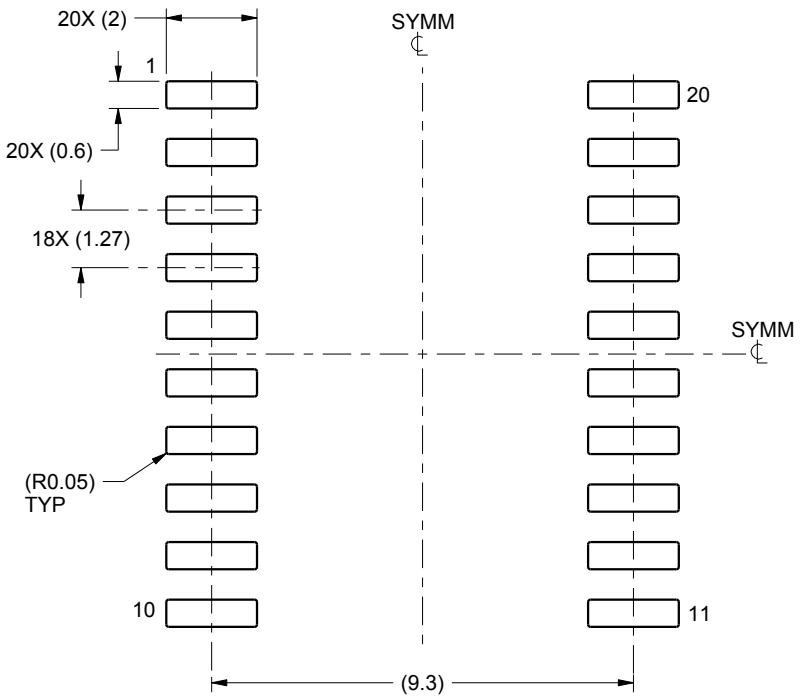
SOIC - 2.65 mm max height

SOIC

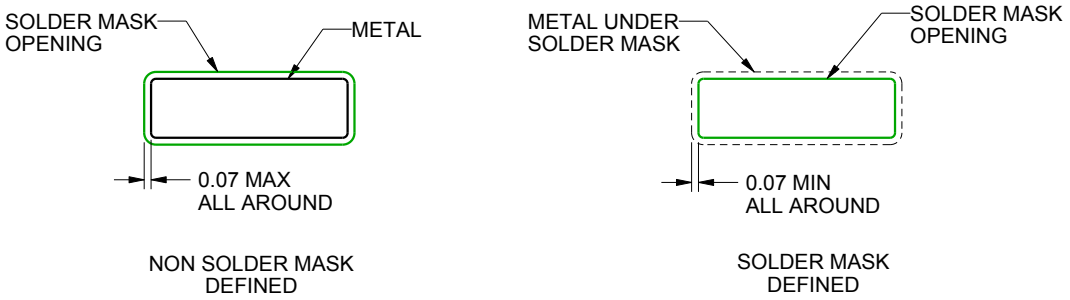


NOTES:

1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
5. Reference JEDEC registration MS-013.



LAND PATTERN EXAMPLE
SCALE:6X

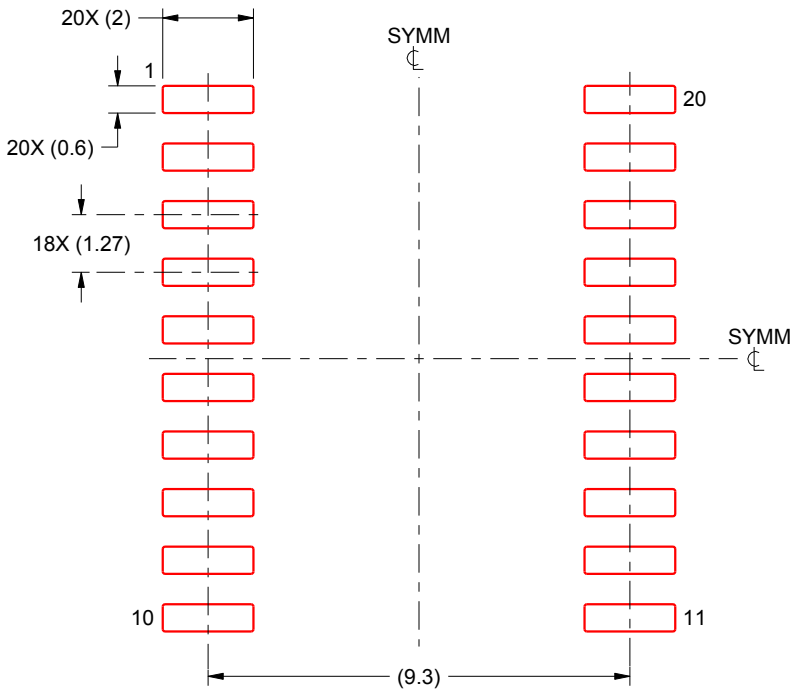


SOLDER MASK DETAILS

4220724/A 05/2016

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:6X

4220724/A 05/2016

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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